AIP | Applied Physics Letters

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Citation: Applied Physics Letters **101**, 132410 (2012); doi: 10.1063/1.4754123
View online: http://dx.doi.org/10.1063/1.4754123
View Table of Contents: http://scitation.aip.org/content/aip/journal/apl/101/13?ver=pdfcov
Published by the AIP Publishing

Magnetic and electronic properties of $D0_{22}$-Mn_3Ge (001) films

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(Received 19 July 2012; accepted 5 September 2012; published online 25 September 2012)

Oriented thin films of Mn_3Ge with the tetragonal $D0_{22}$ structure, grown on strontium titanate substrates, exhibit a low magnetization $M_s = 73\,\text{kA m}^{-1}$ combined with high uniaxial anisotropy $K_u = 0.91\,\text{MJ m}^{-3}$ at 300 K, making them potentially useful for thermally stable sub-10 nm spin torque memory elements. The highly ordered epitaxial Mn_3Ge (001) films show 46% diffusive spin polarization at the Fermi level, measured by point contact Andreev reflection. Density functional calculations show that the compounds are ferrimagnetic, with anisotropic spin polarization at the Fermi level. © *2012 American Institute of Physics*. [http://dx.doi.org/10.1063/1.4754123]

Since the advent of perpendicular magnetic recording and spin torque switching, there is growing interest in magnetic thin film materials with positive uniaxial anisotropy K_u, which have a magnetic easy axis normal to the film surface. Such materials are needed to realize energy-efficient, scalable spin torque memories,[1,2] high-density magnetic recording media,[3] spin logic with integrated memory,[4] and efficient circularly-polarized light emission from spin light-emitting diodes (spin-LEDs).[5,6]

The advantage in the case of spin torque memory arises from the relationship between the critical switching current density j_c and magnetic anisotropy energy $(K_u\text{-}1/2\mu_0 M_s^2)V$ that is directly proportional to the thermal stability.[1] There is no need to overcome an extra shape anisotropy energy barrier during magnetization reversal, and large values of K_u allow for high density scaling. Such devices utilize the transfer of angular momentum carried by spin-polarized conduction electrons to switch the magnetization of the free layer in a nanoscale spin valve (SV) or magnetic tunnel junction (MTJ). The high spin polarization of cubic $L2_1$ Heusler alloys such as Co_2MnSi, Co_2MnGe, and $Co_2Fe(Ge_{0.5}Ga_{0.5})$ has been used to improve spin transfer toque efficiency, and it leads to high magnetoresistance ratios in both SVs and MTJs.[7–13]

Recently, there has been growing interest in manganese-based compounds with the tetragonal $D0_{22}$ structure, which can be regarded as a severely distorted variant of the cubic $L2_1$ structure.[14,15] Alloys in the $Mn_{3-x}Ga$ series with $0 \le x \le 1$ exhibit uniaxial anisotropy, and density-functional calculations indicate a high spin polarization.[16,17] Oriented thin films have been grown, which exhibit perpendicular anisotropy with substantial coercivity,[18–22] useful spin polarization,[22] and low damping[23] which are promising for spin torque magnetic random access memories. Here, we present magnetic and electronic properties of $D0_{22}$-Mn_3Ge (001) epitaxial thin films with perpendicular anisotropy.

Mn-Ge binary compounds can crystallize in as many as eleven different structures with very different magnetic properties.[24,25] Mn_3Ge, the compound of interest here, crystallizes in either the hexagonal $D0_{19}$ structure (ε phase) or the tetragonal $D0_{22}$ structure (ε_1 phase). The high-temperature hexagonal phase is obtained by annealing the material at 700 °C, and quenching. The low-temperature tetragonal phase is obtained by annealing the hexagonal material for 1–2 weeks at 450 °C.[26] Several other non-equilibrium Mn_3Ge structures were also reported, including a cubic α-Mn type solid solution,[27] a cubic $L1_2$ phase,[28,29] and another complex tetragonal phase.[30] The crystal and magnetic structures of the $D0_{19}$ and $D0_{22}$ phases have been determined by Kádár and Krén[26] and Yamada[24,31] using powder neutron diffraction in an off-stoichiometric material of composition $Mn_{3.1}Ge_{0.9}$, which helps to stabilize a single tetragonal $D0_{22}$ phase.[32,33] The lattice parameters of tetragonal $D0_{22}$ unit cell are $a = 3.816$ Å and $c = 7.261$ Å.[26] The magnetic structure determined from the neutron scattering experiments reveals a collinear c-axis ferrimagnetic structure as shown in the inset of Figure 1. The magnetic moments of Mn atoms in 2b and 4d positions are aligned with c-axis and couple antiferromagnetically. Their magnitudes at room temperature were determined to be either $\mu_{2b} = -3.4 \pm 0.3\ \mu_B$ and $\mu_{4d} = 1.9 \pm 0.2\ \mu_B$[26] or $\mu_{2b} = -2.6 \pm 0.3\ \mu_B$ and $\mu_{4d} = 1.8 \pm 0.2\ \mu_B$,[24,31] which give a net magnetization of 0.4 or 1.0 μ_B per formula unit,

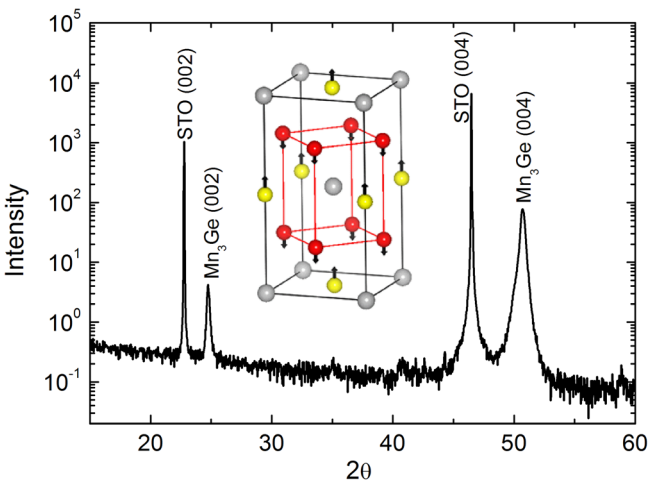

FIG. 1. X-ray diffraction pattern of an epitaxial $D0_{22}$-Mn_3Ge film grown on a $SrTiO_3$ (001) substrate. The inset shows the $D0_{22}$ unit cell of Mn_3Ge. Ge (gray) atoms in 2a positions order in a body-centred tetragonal structure, and Mn atoms occupy 2b (yellow) and 4d (red) sites, which couple antiferromagnetically.

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respectively; 1 μ_B per formula unit corresponds to a magnetization of 175 kA m^{-1} (emu cc^{-1}). The net ferrimagnetic moment is particularly sensitive to any occupancy of the Ge 2*a* site by Mn. For example, exchange of 0.05 atoms per formula unit of the ideal structure from 4*d* to 2*a* sites will reduce the net moment per formula unit by 0.3 μ_B.[24] The $D0_{22}$-Mn_3Ge was found to undergo a structural phase change to the $D0_{19}$ structure at 850 K before reaching its extrapolated the Curie temperature, which is estimated to be 920 K.[26]

We have grown epitaxial $D0_{22}$-Mn_3Ge thin films on $SrTiO_3$ (001) substrates at 450 °C by dc-magnetron sputtering from a Mn_3Ge target. The lattice mismatch between $SrTiO_3$ ($a = 3.905$ Å) and the *a* parameter of tetragonal Mn_3Ge is 2.3%, which allows epitaxial growth of *c*-axis films, as shown by the x-ray diffraction in Figure 1. The lattice parameters obtained from reciprocal space mapping are $a = 3.85 \pm 0.03$ Å and $c = 7.185 \pm 0.007$ Å. Compared to the lattice parameters of the bulk alloy, the unit cell expands in the *ab* plane to facilitate epitaxial growth on the $SrTiO_3$ (001) substrate while shrinking along *c*-axis. The atomic order parameter *S* is defined as the square root of the measured intensity ratio of (101) to (204) reflections, divided by the calculated ratio. It is 0.57 for the as-grown film and 0.82 for the film after annealing at 450 °C for 1 day.

Magnetization measurements on the thin films (Figure 2) show that the crystallographic *c*-axis is the easy axis; the films exhibit substantial coercivity, $\mu_0 H_c = 2.3$ T, and the anisotropy field $\mu_0 H_k$ estimated from room temperature magnetization curves measured in fields of up to 14 T is 25 T. The magnetization of the films is 73 kA m^{-1}, and the anisotropy constant K_u calculated as $\mu_0 H_k M_s/2$ is 0.91 MJ m^{-3}. As in oriented Mn_3Ga films,[22] there is an unusual soft in-plane ferromagnetic component of magnetization, 8 kA m^{-1}, which saturates in a magnetic field of ~60 mT. The soft moment is not seen when the field is applied in the perpendicular direction, and it is therefore not due to a soft ferromagnetic impurity phase present in the films. It may be accounted for by a small, in-plane component of the magnetization of Mn_3Ge, 0.044 μ_B fu^{-1}, which is free to rotate in the basal plane.

The sign of the direct exchange coupling between Mn atoms depends on the interatomic distance; it is usually antiferromagnetic below 2.9 Å.[24] In $D0_{22}$-Mn_3Ge, the distances from a Mn_{4d} atom to the four nearest and two second nearest neighbour Mn_{4d} atoms are 2.698 Å and 3.630 Å, respectively, leading to antiferromagnetic and ferromagnetic coupling. The Mn_{2b}-Mn_{2b} separations are 3.816 Å for the nearest four neighbors and 4.523 Å for the eight second nearest neighbours, which are both ferromagnetic. The short Mn_{2b}-Mn_{4d} distance 2.633 Å (8 nearest neighbors) leads to the strongest antiferromagnetic coupling, which overcomes the antiferromagnetic coupling between nearest neighbor Mn_{4d} spins, and results in the overall ferrimagnetic structure as shown in Figure 1. The small in-plane moment may be a consequence of frustration of some of the exchange bonds.

The spin polarization of the films was measured by point contact Andreev reflection (PCAR)[34,35] at 2 K using a shear-cut Nb tip. The data and the corresponding fit using a modified Blonder-Tinkham-Klapwijk model[36] are shown in Fig 3. Despite the appreciable barrier parameter $Z = 0.36(3)$, the refined value of the spin polarization obtained from measurements on a dozen contacts all agree to yield a spin polarization of the annealed film of 46(2)%, which is greater than that of Fe or Co, but less than we had found previously in $D0_{22}$ Mn_3Ga.[22] A 5.5 K discrepancy between the electronic and lattice temperatures is associated with the high *Z* value.

Electronic structure and magnetic properties of bulk $D0_{22}$ Mn_3Ge were calculated using the full-potential linearized augmented plane-wave (FLAPW) method as implemented in FLEUR code,[36] while the supercell's electronic structures are evaluated using the VASP[37,38] plane-wave based code. In both calculations, we used the Perdew-Burke-Ernzerhof parametrization of the generalized gradient approximation (GGA).[39] The calculated spin-polarized density of states is shown in Fig. 4(a) for the stoichiometric composition (blue lines), and a Mn-rich composition with some Mn on Ge sites (black lines). The net magnetization and spin polarization in the two cases are 177 kA m^{-1} and 75% and 110 kA m^{-1} and 39%, respectively. The latter fits the experimental data quite well, which suggests that the thin films, like the bulk material, are Mn-rich. In addition, the spin polarized Fermi surface for both spin channels, presented in Figs. 4(b) and 4(c), show that

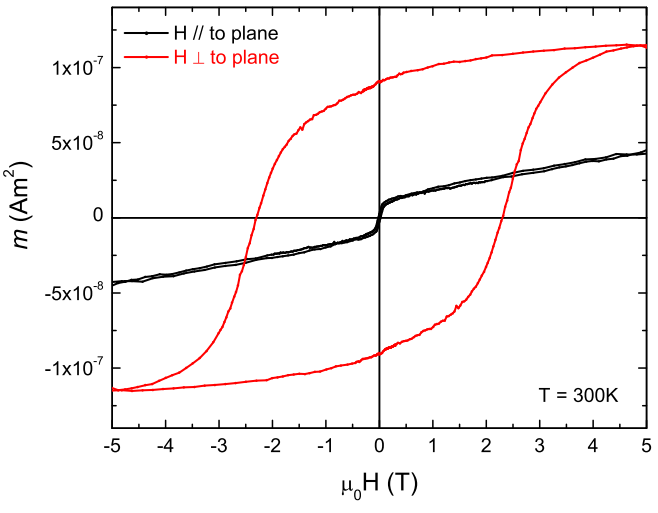

FIG. 2. Magnetization curves for a film of Mn_3Ge at room temperature. The film dimensions are 4.12 mm × 4.18 mm × 100 nm.

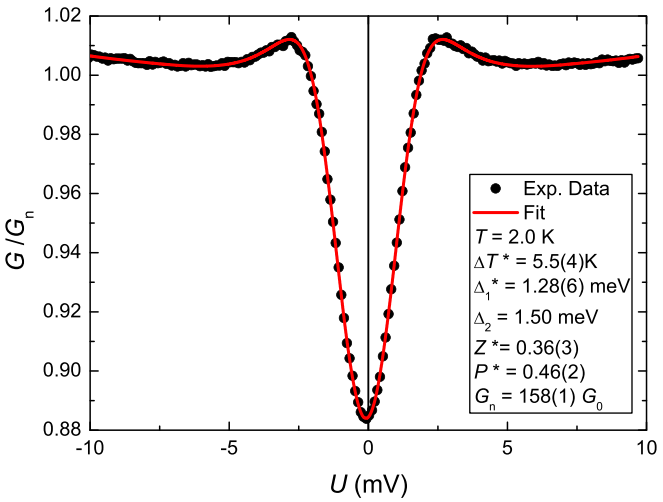

FIG. 3. Point contact Andreev reflection spectroscopy for a *c*-axis oriented $D0_{22}$ Mn_3Ge (001) film. The fitted parameters in the modified BTK model are designated by an asterix.

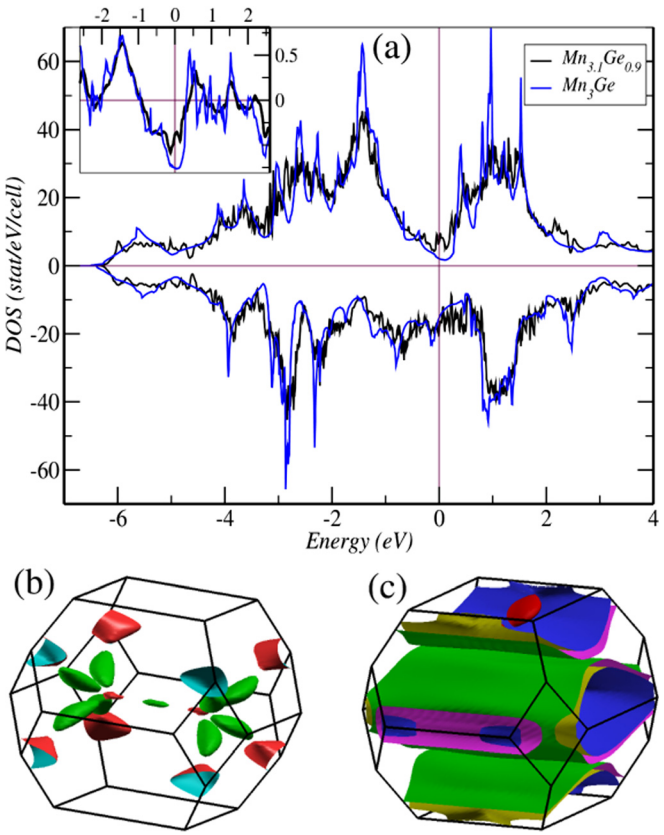

FIG. 4. Top: (a) Spin polarized density of states for $D0_{22}$ Mn_3Ge (blue) and $Mn_{3.1}Ge_{0.9}$ (black). (b) Majority spin and (c) minority spin polarized Fermi surfaces for Mn_3Ge.

Fermi velocity, and therefore the effective spin polarization in Andreev reflection is highly anisotropic. The calculated diffusive Andreev spin polarization (P_2) ranges from 44% to 77% depending on the probing direction. The inclusion of the spin-orbit coupling allows us to calculate the magnetocrystalline anisotropy and we found that $D0_{22}$ Mn_3Ge has a uniaxial anisotropy of the order of 0.8 meV per formula, which corresponds to uniaxial anisotropy constant of 2.4 MJ m^{-3}, which is higher than the measured one. The magnetic and electronic properties are robust against lattice strain.

In conclusion, the large uniaxial anisotropy and useful spin polarization make Mn_3Ge films potential candidates for spin-torque memory applications. The *c*-axis films can be grown directly on $SrTiO_3$ substrates or lattice matching seed layers such as Pd. The stability condition $K_uV/k_BT \geq 60$ is satisfied at room temperature for elements as small as $V = 10 \times 10 \times 2.7$ nm^3. The magnetization is tunable by varying the manganese stoichiometry, and the small co-existing in-plane moment may facilitate spin torque switching.

This work was supported by Science Foundation Ireland as part of the NISE Project (10/IN1.13006), and NanoSci-E+ project "Internet" (08/ERA/I1759), computational resource are provided by TCHPC, and conducted under the framework of the INSPIRE programme, funded by the Irish Government's Programme for Research in Third Level Institutions, Cycle 4, National Development Plan 2007-2013.

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